

Dynamic Characteristics

VRF141G

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 28V$ $f = 1MHz$		400		pF
C_{oss}	Output Capacitance			375		
C_{rss}	Reverse Transfer Capacitance			50		

Functional Characteristics

Symbol	Parameter	Min	Typ	Max	Unit
G_{PS}	$f = 175MHz, V_{DD} = 28V, I_{DQ} = 500mA, P_{out} = 300W$	12	14		dB
η_D	$f = 175MHz, V_{DD} = 28V, I_{DQ} = 500mA, P_{out} = 300W$	45	55		%
Ψ	$f = 175MHz, V_{DD} = 28V, I_{DQ} = 500mA, P_{out} = 300W$ 5:1VSWR - All Phase Angles	No Degradation in Output Power			

1. To MIL-STD-1311 Version A, test method 2204B, Two Tone, Reference Each Tone

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

Typical Performance Curves

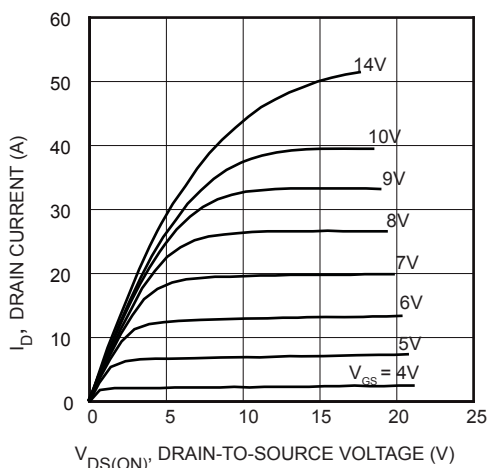


FIGURE 1, Output Characteristics

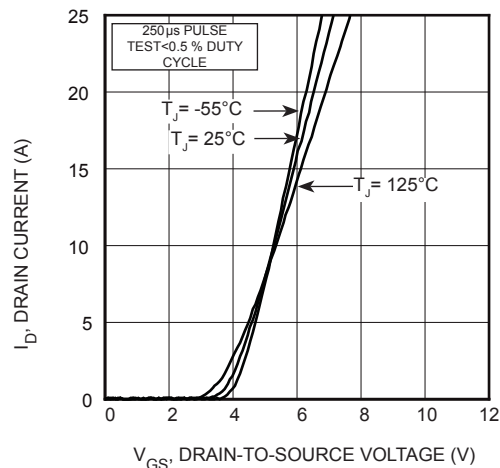


FIGURE 2, Transfer Characteristics

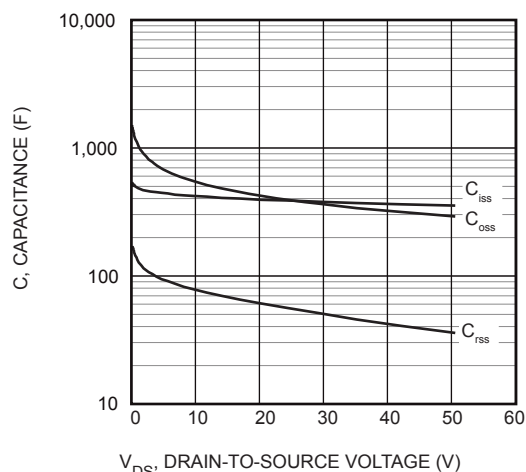


FIGURE 3, Capacitance vs Drain-to-Source Voltage

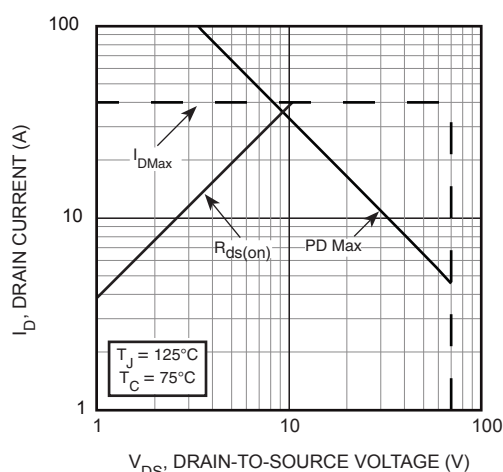


FIGURE 4, Forward Safe Operating Area

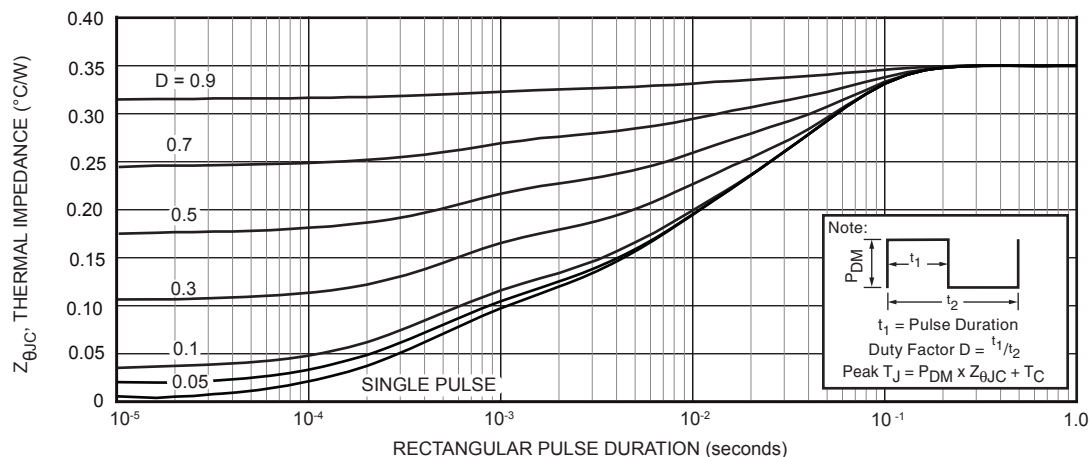
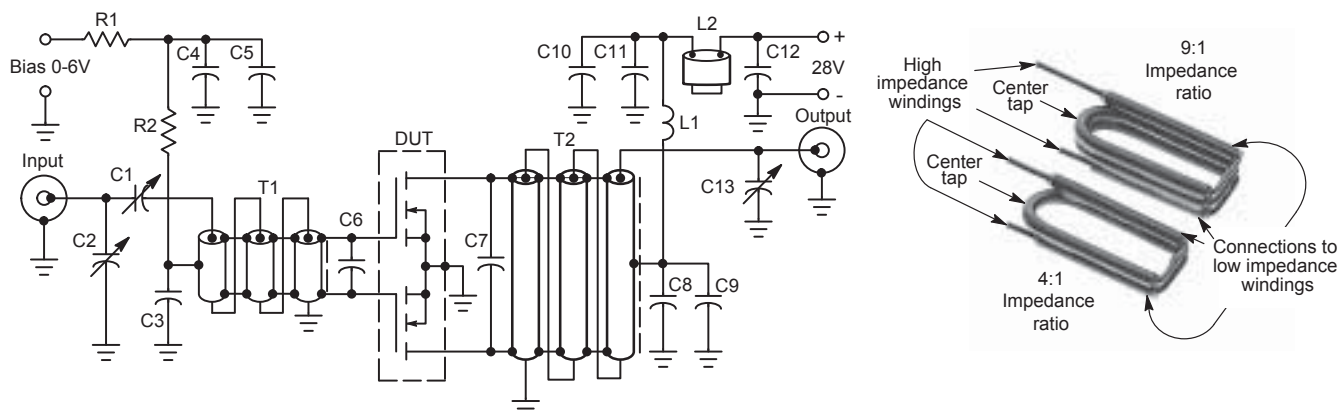


Figure 5. Maximum Effective Transient Thermal Impedance Junction-to-Case vs Pulse Duration



- C1 - Arco 402, 1.5 \pm 20 pF
- C2 - Arco 406, 15 \pm 115 pF
- C3, C4, C8, C9, C10 - 1000 pF Chip
- C5, C11 - 0.1 nF Chip
- C6 - 330 pF Chip
- C7 - 200 pF and 180 pF Chips in Parallel
- C12 - 0.47 nF Ceramic Chip, Kemet 1215 or Equivalent
- C13 - Arco 403, 3.0 \pm 35 pF
- L1 - 10 Turns AWG #16 Enameled Wire, Close Wound, 1/4, I.D.
- L2 - Ferrite Beads of Suitable Material for 1.5 \pm 2.0 nH Total Inductance
- R1 - 100 Ohms, 1/2 W
- R2 - 1.0 kOhm, 1/2 W

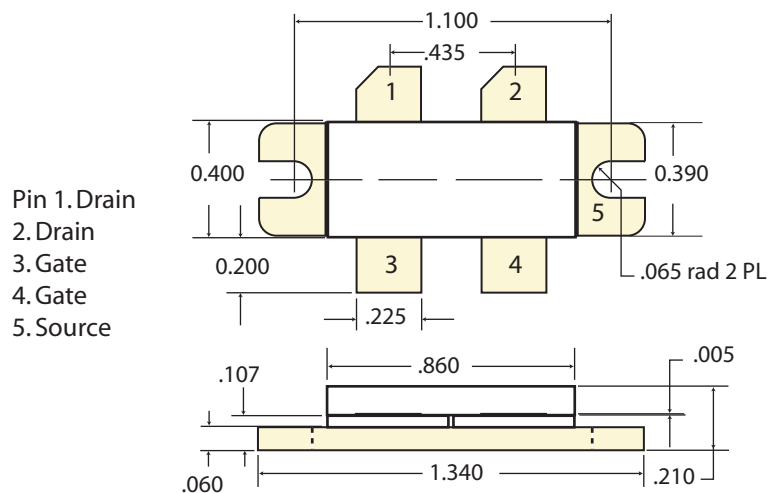
- T1 - 9:1 RF Transformer. Can be made of 15 \pm 18 Ohms Semirigid Co-ax, 62 \pm 90 Mils O.D.
- T2 - 1:9 RF Transformer. Can be made of 15 \pm 18 Ohms Semirigid Co-ax, 70 \pm 90 Mils O.D.

Board Material - 0.062", Fiberglass (G10),
1 oz. Copper Clad, 2 Sides, $\epsilon_r = 5$

NOTE: For stability, the input transformer T1 must be loaded with ferrite toroids or beads to increase the common mode inductance. For operation below 100 MHz. The same is required for the output transformer. See pictures for construction details.

Unless Otherwise Noted, All Chip Capacitors are ATC Type 100B or Equivalent.

Figure 7. 175 MHz Test Circuit



HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and mounting flange is beryllium oxide. Beryllium oxide dust is highly toxic when inhaled. Care must be taken during handling and mounting to avoid damage to this area. These devices must never be thrown away with general industrial or domestic waste.



a  MICROCHIP company

Microsemi Headquarters

One Enterprise, Aliso Viejo,
CA 92656 USA
Within the USA: +1 (800) 713-4113
Outside the USA: +1 (949) 380-6100
Sales: +1 (949) 380-6136
Fax: +1 (949) 215-4996
Email: sales.support@microsemi.com
www.microsemi.com

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